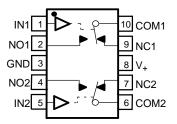
FEATURES

- Isolation in Power-Down Mode, V₁ = 0
- Specified Break-Before-Make Switching
- Low ON-State Resistance (1 Ω)
- Control Inputs Are 5.5-V Tolerant
- Low Charge Injection
- Excellent ON-State Resistance Matching
- Low Total Harmonic Distortion (THD)
- 1.65-V to 5.5-V Single-Supply Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)

APPLICATIONS

- Cell Phones
- PDAs
- Portable Instrumentation
- Audio and Video Signal Routing
- Low-Voltage Data-Acquisition Systems
- Communication Circuits
- Modems
- Hard Drives
- Computer Peripherals
- Wireless Terminals and Peripherals

VSSOP PACKAGE (TOP VIEW)



DESCRIPTION

The TS5A23159 is a dual single-pole double-throw (SPDT) analog switch that is designed to operate from 1.65 V to 5.5 V. The device offers low ON-state resistance and excellent ON-state resistance matching with the break-before-make feature, to prevent signal distortion during the transferring of a signal from one channel to another. The device has an excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

SUMMARY OF CHARACTERISTICS

$$V_{+} = 5 \text{ V}, T_{A} = 25 \text{ }^{\circ}\text{C}$$

Configuration	Dual 2:1 Multiplexer/Demultiplexer (2 × SPDT)
Number of channels	2
ON-state resistance (r _{on})	1.1 Ω
ON-state resistance match (Δr _{on})	0.1 Ω
ON-state resistance flatness (r _{on(flat)})	0.15 Ω
Turn-on/turn-off time (t _{ON} /t _{OFF})	20 ns/15 ns
Break-before-make time (t _{BBM})	12 ns
Charge injection (Q _C)	−7 pC
Bandwidth (BW)	100 MHz
OFF isolation (O _{ISO})	-65 dB at 1 MHz
Crosstalk (X _{TALK})	-66 dB at 1 MHz
Total harmonic distortion (THD)	0.01%
Leakage current (I _{NO(OFF)} /I _{NC(OFF)})	±20 nA
Power-supply current (I ₊)	0.1 μΑ
Package options	10-pin VSSOP



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



ORDERING INFORMATION

T _A	PACKAGE	(1)	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	VSSOP - DGS (MSOP)	Tape and reel	TS5A23159DGSR	JER or JEO

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTION TABLE

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
Н	OFF	ON

Absolute Minimum and Maximum Ratings⁽¹⁾⁽²⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V ₊	Supply voltage range ⁽³⁾		-0.5	6.5	V
$V_{NC} V_{NO} V_{COM}$	Analog voltage range ⁽³⁾⁽⁴⁾⁽⁵⁾		-0.5	V ₊ + 0.5	V
I _K	Analog port diode current	V_{NC} , V_{NO} , $V_{COM} < 0$	-50		mA
I _{NC}	On-state switch current		-200	200	
I _{NO} I _{COM}	On-state peak switch current ⁽⁶⁾	V_{NC} , V_{NO} , $V_{COM} = 0$ to V_{+}	-400	400	mA
VI	Digital input voltage range (3)(4)		-0.5	6.5	V
I _{IK}	Digital input clamp current	V _I < 0	-50		mA
I ₊	Continuous current through V ₊			100	mA
I _{GND}	Continuous current through GND		-100	100	mA
θ_{JA}	Package thermal impedance ⁽⁷⁾	VSSOP package		165	°C/W
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Pulse at 1-ms duration < 10% duty cycle
- (7) The package thermal impedance is calculated in accordance with JESD 51-7.



Electrical Characteristics for 5-V Supply⁽¹⁾

 V_{+} = 4.5 V to 5.5 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch	1	<u> </u>		'					
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	V
Peak ON	_	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C	451/		0.8	1.1	Ω
resistance	r _{peak}	$I_{COM} = -100 \text{ mA},$	See Figure 13	Full	4.5 V			1.5	22
ON-state	r	V_{NO} or $V_{NC} = 2.5 \text{ V}$,	Switch ON,	25°C	4.5 V		0.7	0.9	Ω
resistance	r _{on}	$I_{COM} = -100 \text{ mA},$	See Figure 13	Full	4.5 V			1.1	52
ON-state				25°C			0.05	0.1	
resistance match between channels	$\Delta r_{\sf on}$	V_{NO} or $V_{NC} = 2.5 \text{ V}$, $I_{COM} = -100 \text{ mA}$,	Switch ON, See Figure 13	Full	4.5 V			0.1	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+, \\ I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 13	25°C			0.15		
resistance	r _{on(flat)}	V_{NO} or $V_{NC} = 1 V$,	Switch ON,	25°C	4.5 V		0.1	0.25	Ω
flatness		1.5 V, 2.5 V, I _{COM} = -100 mA,	See Figure 13	Full				0.25	
		V_{NC} or $V_{NO} = 1 V$,		25°C		-20	2	20	
NC, NO OFF leakage current	I _{NO(OFF)} , I _{NC(OFF)}	$V_{COM} = 1 \text{ V to } 4.5 \text{ V,}$ or V_{NC} or $V_{NO} = 4.5 \text{ V,}$ $V_{COM} = 1 \text{ V to } 4.5 \text{ V,}$	Switch OFF, See Figure 14	Full	5.5 V	-100		100	nA
Carron	I _{NC(PWROFF)} ,	V_{NC} or $V_{NO} = 0$ to 5.5 V,	Switch OFF,	25°C	0.17	-1	0.2	1	^
	I _{NO(PWROFF)}	$V_{COM} = 5.5 \text{ V to } 0,$	See Figure 14	Full	0 V	-20		20	μΑ
		V_{NC} or $V_{NO} = 1 V$,		25°C		-20	2	20	
NC, NO ON leakage current	I _{NO(ON)} , I _{NC(ON)}	$V_{COM} = Open,$ or V_{NC} or $V_{NO} = 4.5 V,$ $V_{COM} = Open,$	Switch ON, See Figure 15	Full	5.5 V	-20		20	nA
COM		V_{NC} or $V_{NO} = 0$ to 5.5 V,	Switch ON,	25°C		-1	0.1	1	
OFF leakage current	I _{COM(PWROFF)}	$V_{COM} = 5.5 \text{ V to } 0,$	See Figure 14	Full	0 V	-20		20	μΑ
		V_{NC} or V_{NO} = Open,		25°C		-20	2	20	
COM ON leakage current	I _{COM(ON)}	$V_{COM} = 1 \text{ V},$ or V_{NC} or $V_{NO} = \text{Open},$ $V_{COM} = 4.5 \text{ V},$	Switch ON, See Figure 15	Full	5.5 V	-100		100	nA
Digital Control I	nputs (IN1, IN2) ⁽	(2)			•			,	
Input logic high	V _{IH}			Full		2.4		5.5	V
Input logic low	V _{IL}			Full		0		8.0	V
Input leakage	las la	V _I = 5.5 V or 0		25°C	5.5 V	-2	TBD	2	μА
current	I _{IH} , I _{IL}	V = 0.0 V 01 0		Full	J.J V	100		100	μΛ

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



Electrical Characteristics for 5-V Supply (continued)

 $\rm V_{+} = 4.5~V$ to 5.5 V, $\rm T_{A} = -40^{\circ}C$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONI	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic				l.				,	
		W W	C 25 pF	25°C	5 V	1	8	13	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 17	Full	4.5 V to 5.5 V	1		16.5	ns
		W W	C 25 pF	25°C	5 V	1	5	8	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 17	Full	4.5 V to 5.5 V	1		8	ns
Break-before-		V V V	C 25 pF	25°C	5 V	1	5.5	13	
make time	t _{BBM}	$V_{NC} = V_{NO} = V_{+},$ $R_{L} = 50 \Omega,$	C _L = 35 pF, See Figure 18	Full	4.5 V to 5.5 V	1		14	ns
Charge injection	Q_{C}	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 22	25°C	5 V		-7		рС
NC, NO OFF capacitance	$C_{NC(OFF)}$, $C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 16	25°C	5 V		18		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 16	25°C	5 V		55		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	5 V		54.5		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	5 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	5 V		100		MHz
OFF isolation	O _{ISO}	$R_L = 50 \ \Omega,$ f = 1 MHz,	Switch OFF, See Figure 20	25°C	5 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch ON, See Figure 21	25°C	5 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	5 V		0.004		%
Supply									
Positive				25°C			10	50	
supply current	I ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	Full	5.5 V			750	μΑ



Electrical Characteristics for 3.3-V Supply⁽¹⁾

 $V_{+} = 3 \text{ V}$ to 3.6 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	V
Peak ON		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C	2.1/		1.3	1.6	
resistance	r _{peak}	$I_{COM} = -100 \text{ mÅ},$	See Figure 13	Full	3 V			2	Ω
ON-state	•	V_{NO} or $V_{NC} = 2 V$,	Switch ON,	25°C	3 V		1.2	1.5	Ω
resistance	r _{on}	$I_{COM} = -100 \text{ mA},$	See Figure 13	Full	3 V			1.7	22
ON-state				25°C			0.1	0.15	
resistance match between channels	$\Delta r_{\sf on}$	V_{NO} or $V_{NC} = 2 \text{ V}$, 0.8 V, $I_{COM} = -100 \text{ mA}$,	Switch ON, See Figure 13	Full	3 V		0.2		Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+, \\ I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 13	25°C			0.15		
resistance flatness	$r_{on(flat)}$	V_{NO} or $V_{NC} = 2 \text{ V}, 0.8 \text{ V},$	Switch ON,	25°C	3 V				Ω
nau iess		$I_{COM} = -100 \text{ mA},$	See Figure 13	Full					
		V_{NC} or $V_{NO} = 1 V$,		25°C		-20		2	
NC, NO OFF leakage current	I _{NO(OFF)} , I _{NC(OFF)}	$V_{COM} = 1 \text{ V to 3 V},$ or $V_{NC} \text{ or } V_{NO} = 3 \text{ V},$ $V_{COM} = 1 \text{ V to 3 V},$	Switch OFF, See Figure 14	Full	3.6 V	-50		20	nA
Current	I _{NC(PWROFF)} ,	V_{NC} or $V_{NO} = 0$ to 3.6 V,	Switch OFF,	25°C	0.17	-1		0.2	
	I _{NO(PWROFF)}	$V_{COM} = 3.6 \text{ V to } 0,$	See Figure 14	Full	0 V	-15		15	
		V_{NC} or $V_{NO} = 1 V$,		25°C		-10		4	
NC, NO ON leakage current	I _{NO(ON)} , I _{NC(ON)}	$ \begin{aligned} &V_{COM} = Open, \\ ∨ \\ &V_{NC} \ or \ V_{NO} = 3 \ V, \\ &V_{COM} = Open, \end{aligned} $	Switch ON, See Figure 15	Full	3.6 V	-20		40	nA
COM		V_{NC} or $V_{NO} = 3.6 \text{ V to 0}$,	Switch OFF,	25°C		-1	0.2	1	
OFF leakage current	I _{COM(PWROFF)}	$V_{COM} = 0 \text{ to } 3.6 \text{ V},$	See Figure 14	Full	0 V	-15		15	nA
		V _{NC} or V _{NO} = Open,		25°C		-10	2	10	
COM ON leakage current	I _{COM(ON)}	$V_{COM} = 1 \text{ V},$ or $V_{NC} \text{ or } V_{NO} = \text{Open},$ $V_{COM} = 3 \text{ V},$	Switch ON, See Figure 15	Full	3.6 V	-20		20	nA
Digital Control Inp	outs (IN1, IN2) ⁽²⁾)						,	
Input logic high	V _{IH}			Full		2		5.5	V
Input logic low	V _{IL}			Full		0		8.0	٧
Input leakage cur-	1 1	V _I = 5.5 V or 0		25°C	3.6 V	-2		2	^
rent	I _{IH} , I _{IL}	v ₁ = 5.5 v OI U		Full	3.0 V	20		20	μΑ

 ⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
 (2) All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



Electrical Characteristics for 3.3-V Supply (continued)

 $V_{+} = 3 \text{ V to } 3.6 \text{ V}, T_{A} = -40^{\circ}\text{C to } 85^{\circ}\text{C (unless otherwise noted)}$

PARAMETER	SYMBOL	TEST CONI	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic	1					•		'	
		$V_{COM} = V_+,$	$C_1 = 35 \text{ pF},$	25°C	3.3 V	5	11	19	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 17	Full	3 V to 3.6 V	3		22	ns
		V - V	C = 25 pE	25°C	3.3 V	1	5	9	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 17	Full	3 V to 3.6 V	1		9	ns
Break-before-		$V_{NC} = V_{NO} = V_{+}$	$C_1 = 35 pF$,	25°C	3.3 V	1	7	17	
make time	t _{BBM}	$R_L = 50 \Omega,$	See Figure 18	Full	3 V to 3.6 V	1		20	ns
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 22	25°C	3.3 V		-4		рС
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 16	25°C	3.3 V		18		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch ON,	See Figure 16	25°C	3.3 V		56		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	3.3 V		56		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	3.3 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	3.3 V		100		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, See Figure 20	25°C	3.3 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 21	25°C	3.3 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	3.3 V		0.01		%
Supply					•				
Positive supply current	I ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	3.6 V			25 150	nA



Electrical Characteristics for 2.5-V Supply⁽¹⁾

 V_{+} = 2.3 V to 2.7 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	ITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Analog Switch	•			1					
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	V
Peak ON resistance	r _{peak}	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -8 \text{ mA},$	Switch ON, See Figure 13	25°C Full	2.3 V		1.8	2.5	Ω
ON-state resistance	r _{on}	V_{NO} or V_{NC} = 1.8 V, I_{COM} = -8 mA,	Switch ON, See Figure 13	25°C Full	2.3 V		1.5	2.4	Ω
ON-state				25°C			0.15	0.2	
resistance match between channels	$\Delta r_{\sf on}$	V_{NO} or V_{NC} = 1.8 V, 0.8 V, I_{COM} = -8 mA,	Switch ON, See Figure 13	Full	2.3 V			0.2	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -8 \text{ mA},$	Switch ON, See Figure 13	25°C			0.6		
resistance flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 0.8 \text{ V}$, 1.8 V,	Switch ON,	25°C	2.3 V		0.6	1	Ω
nautess		$I_{COM} = -8 \text{ mA},$	See Figure 13	Full				1	
		V_{NC} or $V_{NO} = 0.5 \text{ V}$,		25°C		-20	2	20	
NC, NO OFF leakage current	I _{NO(OFF)} , I _{NC(OFF)}	$V_{COM} = 0.5 \text{ V to } 2.3 \text{ V,}$ or $V_{NC} \text{ or } V_{NO} = 2.2 \text{ V,}$ $V_{COM} = 0.5 \text{ V to } 2.3 \text{ V,}$	Switch OFF, See Figure 14	Full	2.3 V	-50		50	nA
Carront	I _{NC(PWROFF)} ,	V_{NC} or $V_{NO} = 0$ to 2.7 V,	Switch OFF,	25°C	0.17	-1	0.1	1.0	۸
	I _{NO(PWROFF)}	$V_{COM} = 2.7 \text{ V to 0},$	See Figure 14	Full	0 V	-10		10	μΑ
		V_{NC} or $V_{NO} = 0.5 \text{ V}$,		25°C		-10	2	10	
NC, NO ON leakage current	I _{NO(ON)} , I _{NC(ON)}	$\begin{aligned} & V_{COM} = Open, \\ & or \\ & V_{NC} \text{ or } V_{NO} = 2.2 \text{ V}, \\ & V_{COM} = Open, \end{aligned}$	Switch ON, See Figure 15	Full	2.7 V	-20		20	nA
COM		V_{NC} or $V_{NO} = 2.7 \text{ V to } 0$,	Switch OFF,	25°C		-1	0.1	1	
OFF leakage current	I _{COM(PWROFF)}	$V_{COM} = 0$ to 2.7 V,	See Figure 14	Full	0 V	-10		10	nA
		V_{NC} or V_{NO} = Open,		25°C		-10	2	10	
COM ON leakage current	I _{COM(ON)}	$\begin{aligned} &V_{COM} = 0.5 \text{ V,} \\ &\text{or} \\ &V_{NC} \text{ or } V_{NO} = \text{Open,} \\ &V_{COM} = 2.2 \text{ V,} \end{aligned}$	Switch ON, See Figure 15	Full	2.7 V	-20		20	nA
Digital Control In	puts (IN1, IN2) ⁽²⁾							'	
Input logic high	V _{IH}			Full		1.8		5.5	V
Input logic low	V _{IL}			Full		0		0.6	V
Input leakage	1 1	V = 5.5 V or 0		25°C	2.7 V	-2		2	^
current	I _{IH} , I _{IL}	$V_1 = 5.5 \text{ V or } 0$		Full	2.1 V	20		20	μΑ

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



Electrical Characteristics for 2.5-V Supply⁽¹⁾ (Continued)

 $V_{+} = 2.3 \text{ V to } 2.7 \text{ V}, T_{A} = -40^{\circ}\text{C} \text{ to } 85^{\circ}\text{C} \text{ (unless otherwise noted)}$

PARAMETER	SYMBOL	TEST CONE	DITIONS	TA	٧,	MIN	TYP	MAX	UNIT
Dynamic	1	1				Į.			
		V V	C 25 pF	25°C	2.5 V	5	15	28	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	$C_L = 35 \text{ pF},$ See Figure 17	Full	2.3 V to 2.7 V	5		32	ns
		V V	C _L = 35 pF,	25°C	2.5 V	2	6	9	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 17	Full	2.3 V to 2.7 V	2		10	ns
Break-before-		V V V	C 25 pF	25°C	2.5 V	1	10	27	
make time	t _{BBM}	$V_{NC} = V_{NO} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 18	Full	2.3 V to 2.7 V	1		30	ns
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 22	25°C	2.5 V		-3		рС
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 16	25°C	2.5 V		18.5		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch ON,	See Figure 16	25°C	2.5 V		56.5		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	2.5 V		56.5		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	2.5 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	2.5 V		100		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch OFF, See Figure 20	25°C	2.5 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 21	25°C	2.5 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	2.5 V		0.02		%
Supply								l.	
Positive supply current	I ₊	$V_1 = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	2.7 V		10	25 100	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum



Electrical Characteristics for 1.8-V Supply⁽¹⁾

 V_{+} = 1.65 V to 1.95 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	ITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Analog Switch				U.	II.				
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	V
Peak ON	_	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C	1 CE V		5		Ω
resistance	r _{peak}	$I_{COM} = -2 \text{ mA},$	See Figure 13	Full	1.65 V			15	22
ON-state	_	V_{NO} or $V_{NC} = 1.5 \text{ V}$,	Switch ON,	25°C	1.65 V		2	2.5	Ω
resistance	r _{on}	$I_{COM} = -2 \text{ mA},$	See Figure 13	Full	1.05 V			3.5	22
ON-state				25°C			0.15	0.4	
resistance match between channels	$\Delta r_{\sf on}$	V_{NO} or V_{NC} = 0.6 V, 1.5 V, I_{COM} = -2 mA,	Switch ON, See Figure 13	Full	1.65 V			0.4	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 13	25°C			5		
resistance flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 0.6 \text{ V}$, 1.5 V,	Switch ON,	25°C	1.65 V		4.5		Ω
natricss		$I_{COM} = -2 \text{ mA},$	See Figure 13	Full					
		V_{NC} or $V_{NO} = 0.3 \text{ V}$,		25°C		-20	2	20	
NC, NO OFF leakage	I _{NO(OFF)} , I _{NC(OFF)}	$V_{COM} = 0.3 \text{ V to } 1.65 \text{ V},$ or $V_{NC} \text{ or } V_{NO} = 1.65 \text{ V},$ $V_{COM} = 0.3 \text{ V to } 1.65 \text{ V}$	Switch OFF, See Figure 14	Full	1.65 V	-50		50	nA
current	1	V_{NC} or $V_{NO} = 0$ to	Switch OFF,	25°C		-1	0.1	1	
	I _{NC(PWROFF)} , I _{NO(PWROFF)}	1.95 V, V _{COM} = 1.95 V to 0,	See Figure 14	Full	0 V	-5		5	μΑ
NO NO		V_{NC} or $V_{NO} = 0.3 \text{ V}$,		25°C		- 5	2	5	
NC, NO ON leakage current	I _{NO(ON)} , I _{NC(ON)}	$V_{COM} = Open,$ or V_{NC} or $V_{NO} = 1.65 V,$ $V_{COM} = Open,$	Switch ON, See Figure 15	Full	1.95 V	-20		20	nA
COM		V_{NC} or $V_{NO} = 1.95 \text{ V to } 0$,	Switch OFF,	25°C		-1	0.1	1	
OFF leakage current	I _{COM(PWROFF)}	$V_{COM} = 0 \text{ to } 1.95 \text{ V},$	See Figure 14	Full	0 V	-5		5	μΑ
		V _{NC} or V _{NO} = Open,		25°C		-10	2	10	
COM ON leakage current	I _{COM(ON)}	$V_{COM} = 0.3 \text{ V},$ or $V_{NC} \text{ or } V_{NO} = \text{Open},$ $V_{COM} = 1.65 \text{ V},$	Switch ON, See Figure 15	Full	1.95 V	-20		20	nA
Digital Control In	puts (IN1, IN2) ⁽²⁾)						'	
Input logic high	V _{IH}			Full		1.5		5.5	V
Input logic low	V _{IL}			Full		0		0.6	V
Input leakage	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C	1.95 V	-2		2	μА
current	יורוי יונ	1 3.3 . 3. 0		Full		20		20	L., ,

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



Electrical Characteristics for 1.8-V Supply⁽¹⁾ (Continued)

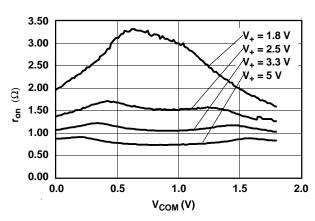
 V_{+} = 1.65 V to 1.95 V, T_{A} = -40°C to 85°C (unless otherwise noted)

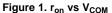
PARAMETER	SYMBOL	TEST CONE	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic								,	
		V V	0 25 -5	25°C	1.8 V	10	27.5	48.5	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	$C_L = 35 \text{ pF},$ See Figure 17	Full	1.65 V to 1.95 V	10		55	ns
		V V	C 25 pF	25°C	1.8 V	2	6.5	11	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 17	Full	1.65 V to 1.95 V	2		12	ns
Break-before-		V V V	C 25 pF	25°C	1.8 V	1	18	50	
make time	t _{BBM}	$V_{NC} = V_{NO} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 18	Full	1.65 V to 1.95 V	1		55	ns
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 22	25°C	1.8 V		2		рС
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 16	25°C	1.8 V		18.5		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch ON,	See Figure 16	25°C	1.8 V		56.5		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	1.8 V		56.5		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	1.8 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	1.8 V		105		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, See Figure 20	25°C	1.8 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch ON, See Figure 21	25°C	1.8 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	1.8 V		0.06		%
Supply		·			•				
Positive supply current	I ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	1.95 V		10	25 050	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum



TYPICAL PERFORMANCE





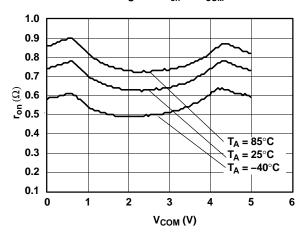


Figure 3. r_{on} vs V_{COM} ($V_{+} = 5$ V)

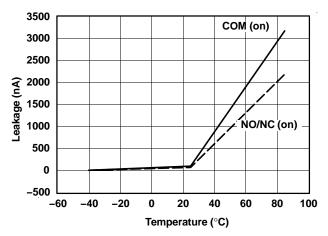
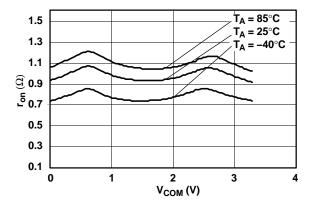


Figure 5. Leakage Current vs Temperature (V₊ = 5 V)



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Figure 2. r_{on} vs V_{COM} ($V_{+} = 3.3 \text{ V}$)

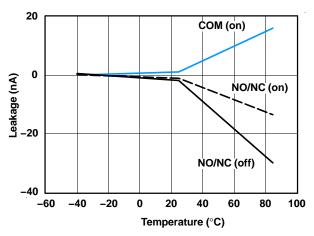


Figure 4. Leakage Current vs Temperature (V₊ = 3.3 V)

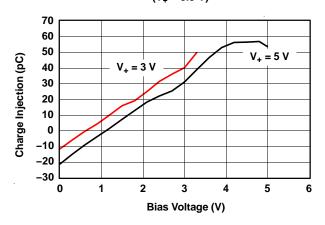


Figure 6. Charge Injection (Q_C) vs V_{COM}

TYPICAL PERFORMANCE (continued)

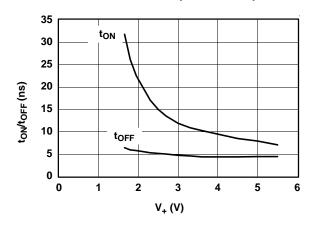


Figure 7. t_{ON} and t_{OFF} vs Supply Voltage

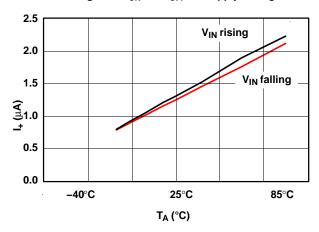


Figure 9. t_{ON} and t_{OFF} vs Temperature

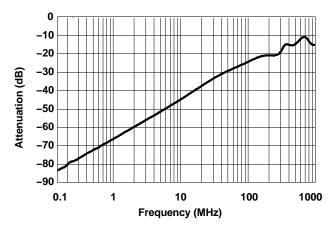


Figure 11. OFF Isolation vs Frequency

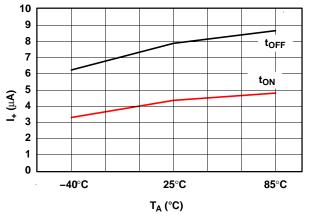


Figure 8. t_{ON} and t_{OFF} vs Temperature

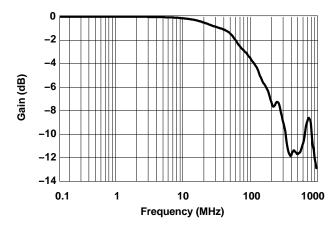


Figure 10. Bandwidth $(V_+ = 5 V)$

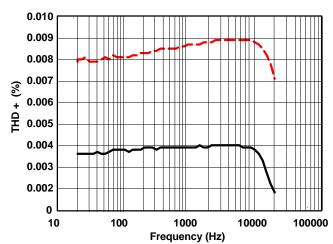


Figure 12. Total Harmonic Distortion vs Frequency $(V_+ = 5 \text{ V})$

TYPICAL PERFORMANCE (continued)

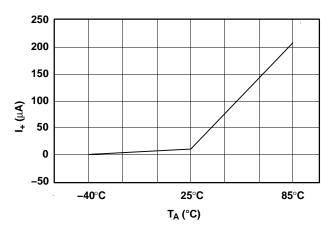


Figure 13. Power-Supply Current vs Temperature $(V_+ = 5 V)$

PIN DESCRIPTION

PIN NO.	NAME	DESCRIPTION
1	IN1	Digital control pin to connect COM to NO or NC
2	NO1	Normally open
3	GND	Digital ground
4	NO2	Normally open
5	IN2	Digital control to connect COM to NO or NC
6	COM2	Common
7	NC2	Normally closed
8	V ₊	Power supply
9	NC1	Normally closed
10	COM1	Power supply



PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION					
V_{COM}	Voltage at COM					
V _{NC}	Voltage at NC					
V _{NO}	Voltage at NO					
r _{on}	Resistance between COM and NC or COM and NO ports when the channel is ON					
r _{peak}	Peak on-state resistance over a specified voltage range					
Δr_{on}	Difference of r _{on} between channels in a specific device					
r _{on(flat)}	Difference between the maximum and minimum value of r _{on} in a channel over the specified range of conditions					
I _{NC(OFF)}	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions					
I _{NC(PWROFF)}	Leakage current measured at the NC port during the power-down condition, $V_{+} = 0$					
I _{NO(OFF)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions					
I _{NO(PWROFF)}	Leakage current measured at the NO port during the power-down condition, $V_{+} = 0$					
I _{NC(ON)}	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open					
I _{NO(ON)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open					
I _{COM(ON)}	Leakage current measured at the COM port, with the corresponding channel (COM to NO or COM to NC) in the ON state and the output (NC or NO) open					
I _{COM(PWROFF)}	Leakage current measured at the COM port during the power-down condition, $V_{+} = 0$					
V_{IH}	Minimum input voltage for logic high for the control input (IN)					
V_{IL}	Maximum input voltage for logic low for the control input (IN)					
V_{I}	Voltage at the control input (IN)					
$I_{\rm IH},~I_{\rm IL}$	Leakage current measured at the control input (IN)					
t _{ON}	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON.					
t _{OFF}	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFF.					
t _{BBM}	Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state.					
$Q_{\mathbb{C}}$	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NO or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta \ V_{COM}$, C_L is the load capacitance and ΔV_{COM} is the change in analog output voltage.					
$C_{NC(OFF)}$	Capacitance at the NC port when the corresponding channel (NC to COM) is OFF					
$C_{NO(OFF)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is OFF					
C _{NC(ON)}	Capacitance at the NC port when the corresponding channel (NC to COM) is ON					
C _{NO(ON)}	Capacitance at the NO port when the corresponding channel (NO to COM) is ON					
C _{COM(ON)}	Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON					
C _I	Capacitance of control input (IN)					
O _{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state.					
X _{TALK}	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB.					
BW	Bandwidth of the switch. This is the frequency in which the gain of an ON channel is -3 dB below the DC gain.					
THD	Total harmonic distortion is defined as the ratio of the root mean square (RMS) value of the second, third, and higher harmonics to the magnitude of fundamental harmonic.					
I ₊	Static power-supply current with the control (IN) pin at V ₊ or GND					



PARAMETER MEASUREMENT INFORMATION

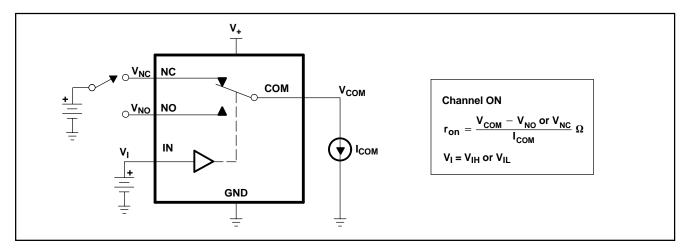


Figure 14. ON-State Resistance (ron)

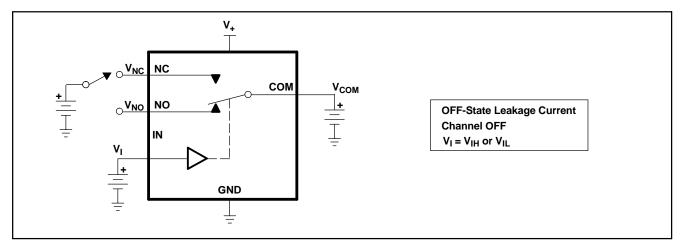


Figure 15. OFF-State Leakage Current (I_{NC(OFF)}, I_{NO(OFF)}, I_{NO(OFF)}, I_{NO(OFF)}, I_{COM(OFF)}, I_{COM(OFF)}, I_{COM(OFF)})

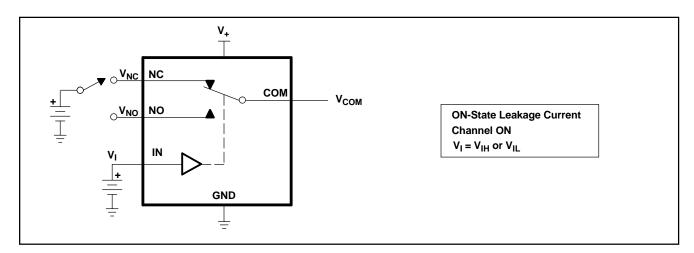


Figure 16. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NC(ON)}$, $I_{NO(ON)}$)



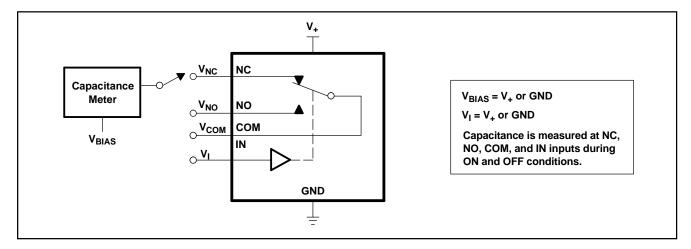
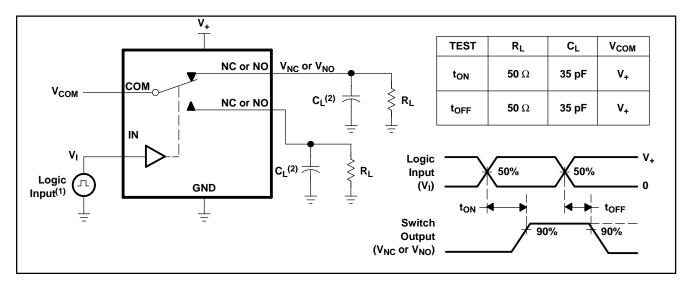


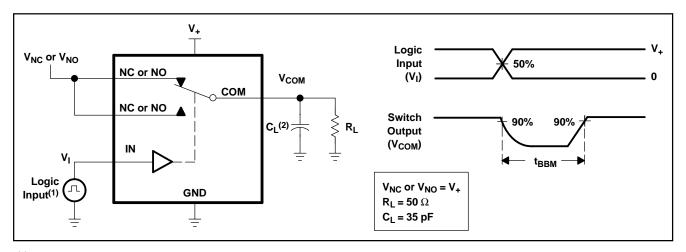
Figure 17. Capacitance (C_I, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NO(OFF)}$, $C_{NC(ON)}$, $C_{NO(ON)}$)



- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.
- (2) C_L includes probe and jig capacitance.

Figure 18. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})





- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f < 5$ ns. $t_f < 5$ ns.
- (2) C_L includes probe and jig capacitance.

Figure 19. Break-Before-Make Time (t_{BBM})

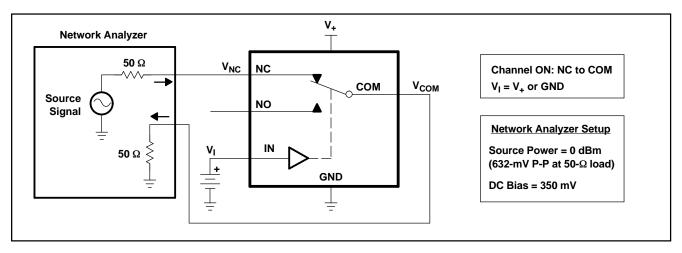


Figure 20. Bandwidth (BW)



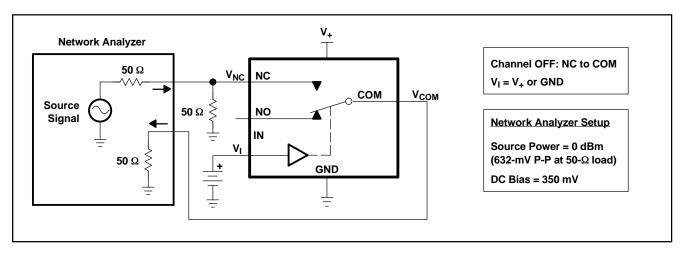


Figure 21. OFF Isolation (O_{ISO})

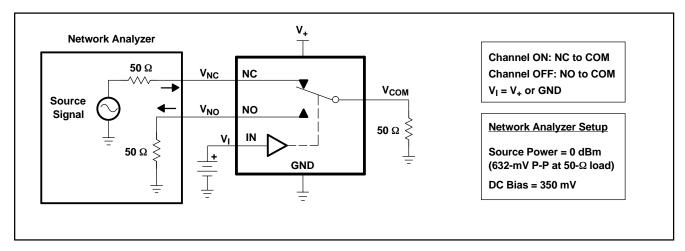
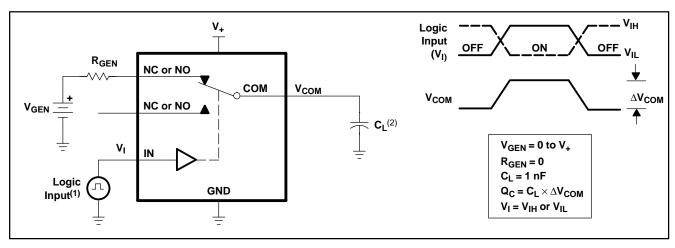


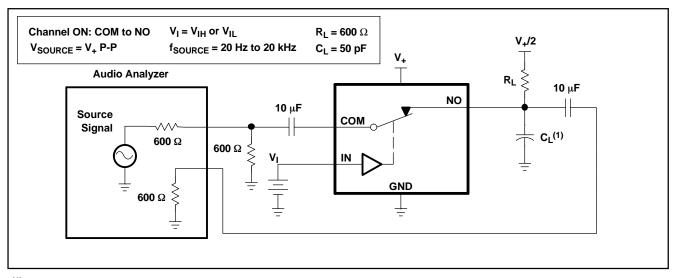
Figure 22. Crosstalk (X_{TALK})





- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r < 5 ns. t_f < 5 ns.
- (2) C_L includes probe and jig capacitance.

Figure 23. Charge Injection (Q_C)



(1) C_L includes probe and jig capacitance.

Figure 24. Total Harmonic Distortion (THD)



THERMAL PAD MECHANICAL DATA

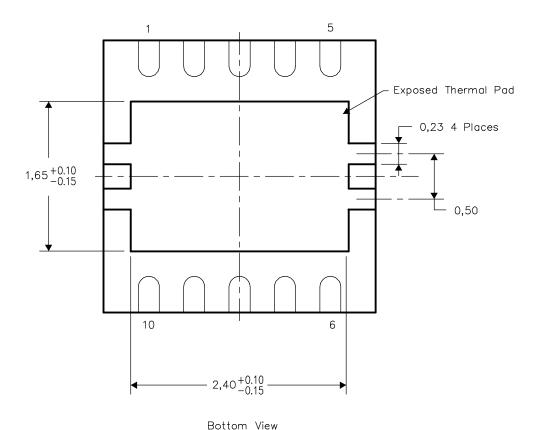
DRC (S-PDSO-N10)

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB), the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to a ground plane or special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, Quad Flatpack No—Lead Logic Packages, Texas Instruments Literature No. SCBA017. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions





com 24-Aug-2005

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins P	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TS5A23159DGSR	ACTIVE	MSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A23159DGST	ACTIVE	MSOP	DGS	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in

a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS) or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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DGS (S-PDSO-G10)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation BA.



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